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D		G	J			I
			A "	H "	A "	
	°C					
	°C					
	°C					
	°C					
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	°C					

C

	A	D	K		D

H

H

FIG.1:Power dissipation vs. on-state current
(per thyristor or diode)

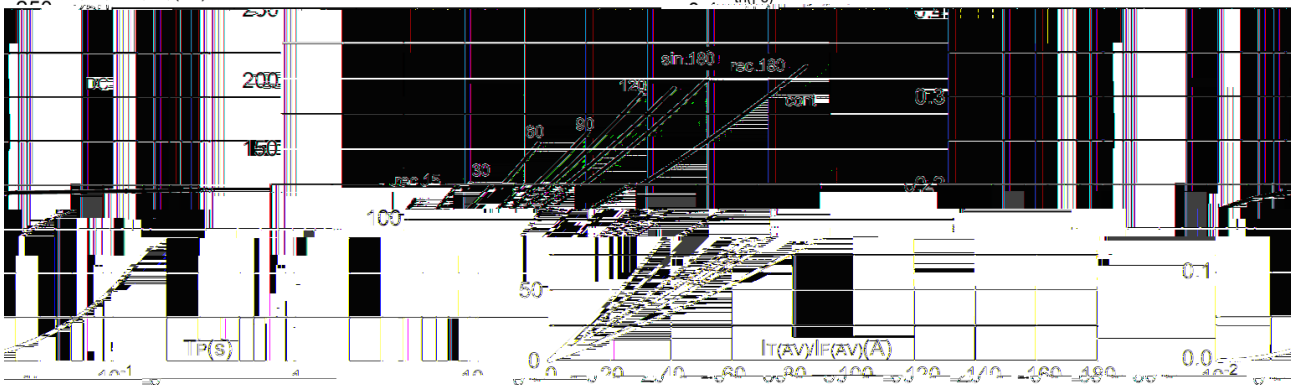
 $P_T(A_V)/P_F(A_V)(W)$


FIG.2: Maximum transient thermal impedance
junction to case(per thyristor or diode)

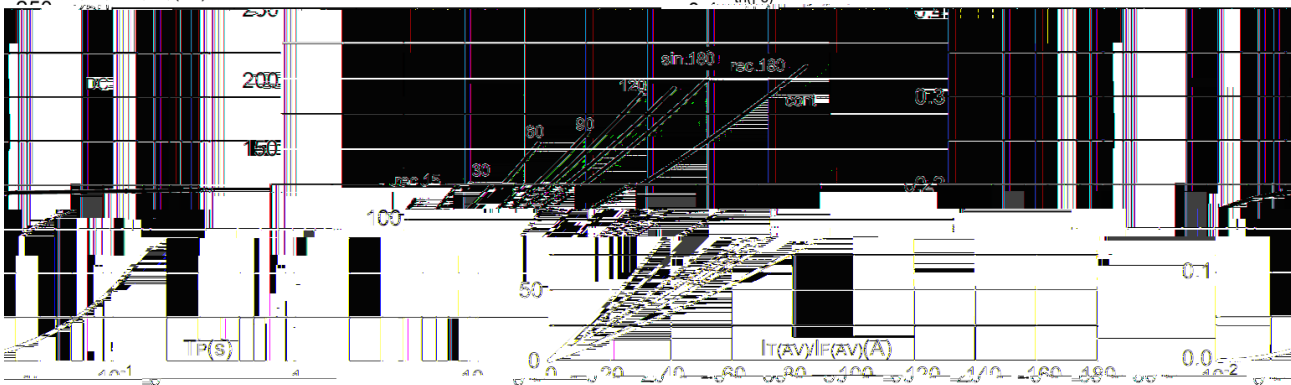
 $R_{th(j-c)}(^{\circ}C/W)$


FIG.3:Forward characteristics
(per thyristor or diode)

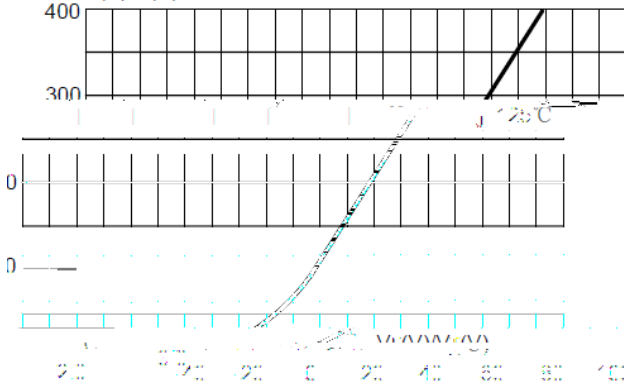
 $I_F(A)/I_T(A)$


FIG.4: Relative variations of gate trigger current, holding current and latching current versus junction temperature

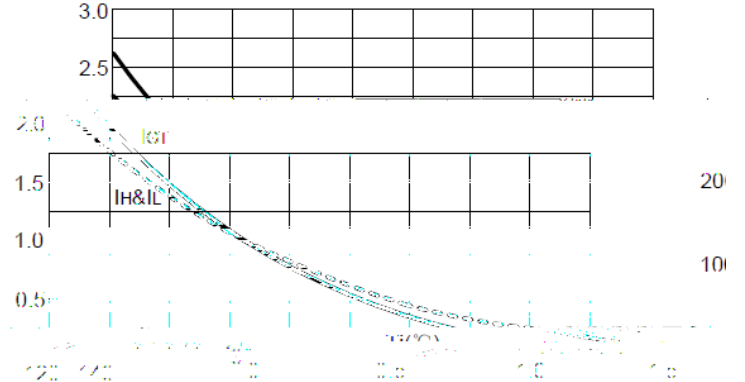
 $I_{GT, IH, IL(T_j)}/I_{GT, IH, IL(T_j=25^{\circ}C)}$


FIG.5: Gate trigger characteristics

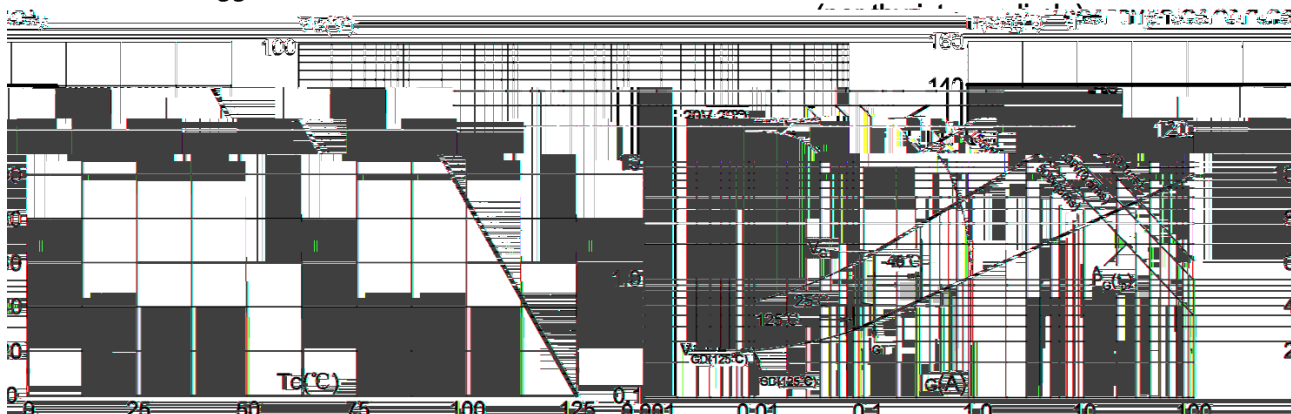
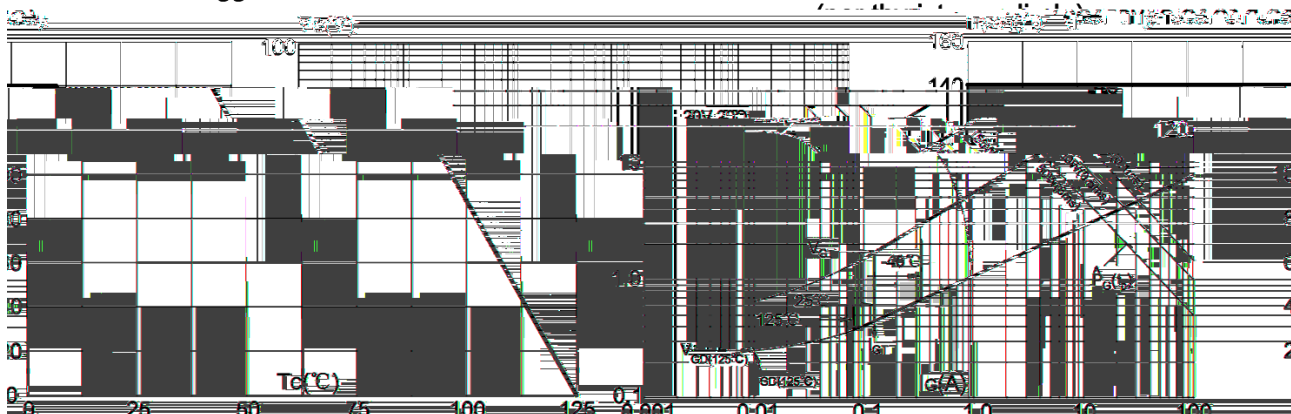
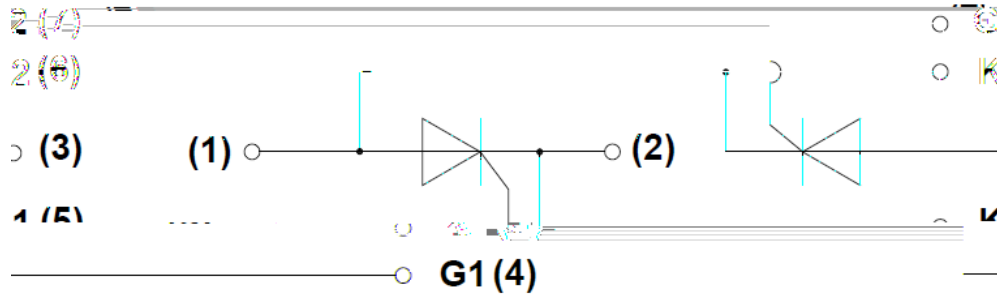


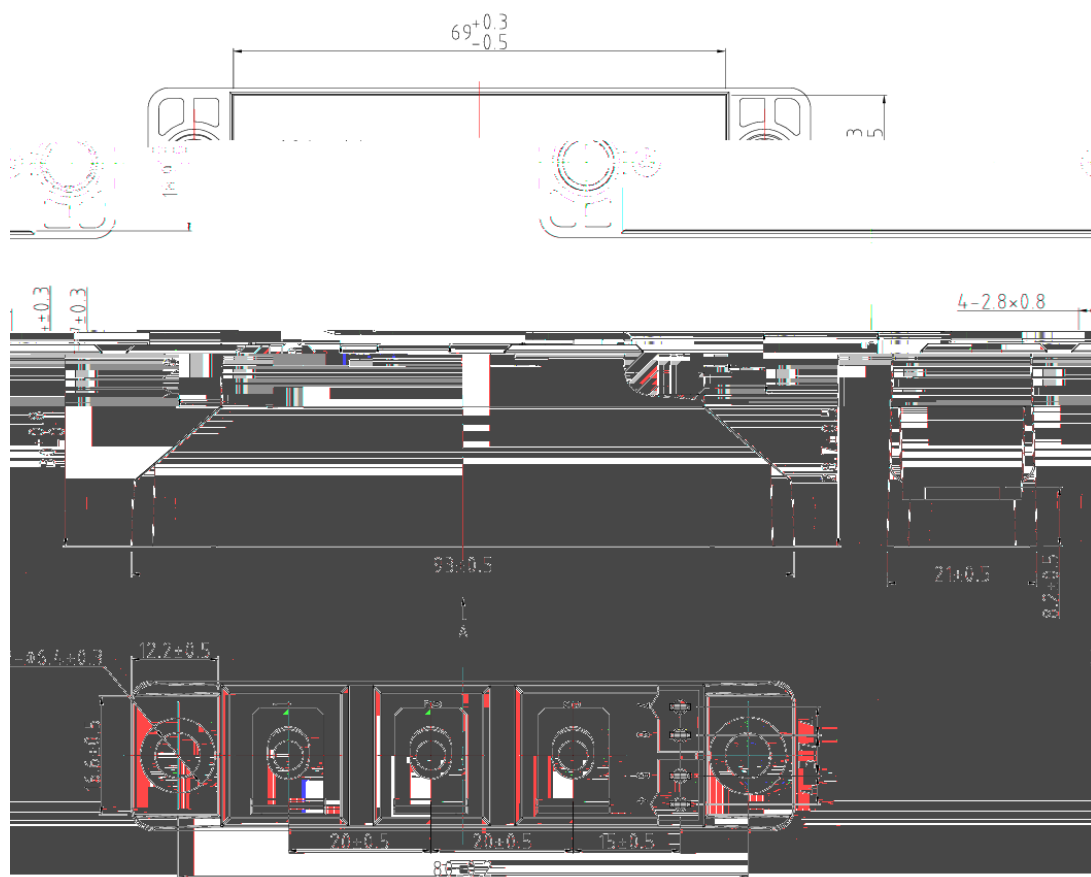
FIG.6: Forward current vs. case temperature





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